Product data sheet

1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

2. Features and benefits

- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state losses
- Fast switching
- High thermal cycling performance
- Low thermal resistance
- Low forward voltage drop

3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		400				V
I _{O(AV)}	average output current	SQW; δ = 0.5; $T_{mb} \le$ 115 °C; both diodes conducting; Fig. 1; Fig. 2	20				А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 115 °C$; per diode	20				А
I _{FSM}	non-repetitive peak	SIN; $t_p = 10 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; per diode	120				Α
	forward current	SIN; $t_p = 8.3 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; per diode	132			Α	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>		-	0.87	1.05	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6; Fig. 7$		-	50	60	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode		A
3	A2	anode 2		A1 A2 K sym125

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BYV34-400	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV34-400	BYV34-400

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		400	V
V_{RWM}	crest working reverse voltage		400	V
V_R	reverse voltage	T _{mb} ≤ 138 °C; DC	400	V
$I_{O(AV)}$	average output current	SQW; δ = 0.5; $T_{mb} \le$ 115 °C; both diodes conducting; Fig. 1; Fig. 2	20	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 115 °C$; per diode	20	А
I _{FSM}	non-repetitive peak	SIN; t_p = 10 ms; $T_{j(init)}$ = 25 °C; per diode	120	А
	forward current	SIN; t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; per diode	132	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

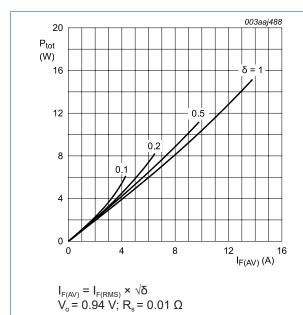
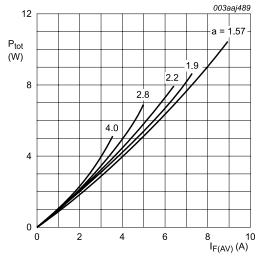


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 0.94 V; R_s = 0.01 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to	with heatsink compound; both diodes conducting		-	-	1.6	K/W
	mounting base	with heatsink compound; per diode; Fig. 3		-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient			-	60	-	K/W

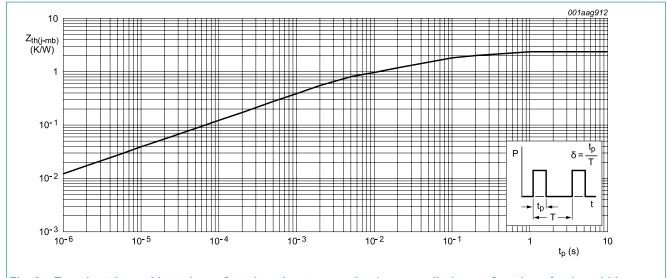


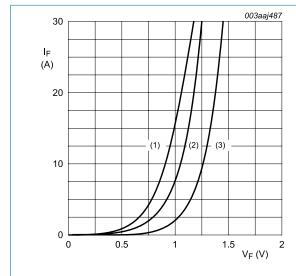
Fig. 3. Transient thermal impedance from junction to mounting base per diode as a function of pulse width

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10. Characteristics

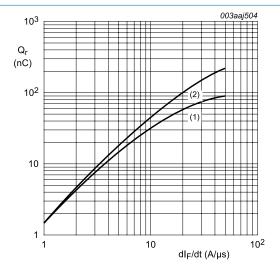
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.1	1.35	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.87	1.05	V
I _R reverse current	reverse current	-	10	50	μA	
		V _R = 400 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics			'		'
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; Fig. 5; Fig. 6	-	50	50	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6; Fig. 7	-	50	60	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 6; Fig. 8$	-	4	5	А
V _{FRM}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 9	-	2.5	-	V



(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values V_o = 0.94 V; R_s = 0.01 Ω

Fig. 4. Forward current as a function of forward voltage; per diode



(1) $I_F = 2 \text{ A}$; $T_j = 25 \text{ °C}$ (2) $I_F = 20 \text{ A}$; $T_j = 25 \text{ °C}$

Fig. 5. Recovered charge as a function of rate of change of forward current; per diode; maximum values

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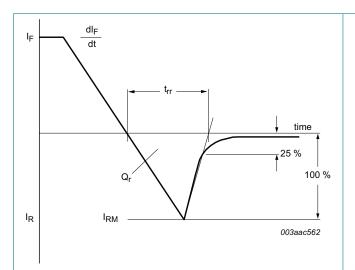
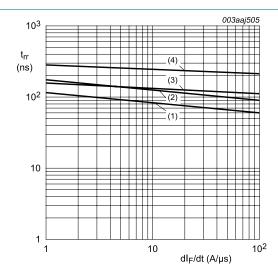


Fig. 6. Reverse recovery definitions; ramp recovery



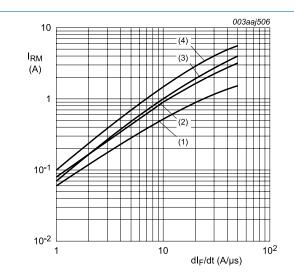
(1)
$$I_F = 1 \text{ A}$$
; $T_j = 25 ^{\circ}\text{C}$

(2)
$$I_F = 1 \text{ A}; T_j = 100 ^{\circ}\text{C}$$

(3)
$$I_F = 20 \text{ A}$$
; $T_i = 25 \text{ °C}$

(4)
$$I_F = 20 \text{ A}$$
; $T_j = 100 \text{ °C}$

Fig. 7. Reverse recovery time as a function of rate of change of forward current; per diode; maximum values



(1) $I_F = 1 A$; $T_i = 25 °C$

(2) $I_F = 1 A$; $T_j = 100 \,^{\circ}C$

(3) $I_F = 20 \text{ A}$; $T_j = 25 \text{ °C}$

(4) $I_F = 20 \text{ A}$; $T_i = 100 \text{ °C}$



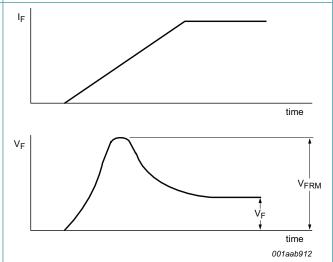
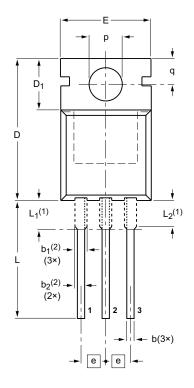


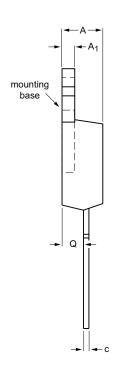
Fig. 9. Forward recovery definitions

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13	

Dual ultrafast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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